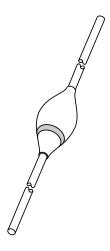
### **DISCRETE SEMICONDUCTORS**

# DATA SHEET



# **BYX120G**High-voltage soft-recovery controlled avalanche rectifier

Product specification
Supersedes data of May 1996
File under Discrete Semiconductors, SC01

1996 Sep 26





### High-voltage soft-recovery controlled avalanche rectifier

### **BYX120G**

### **FEATURES**

- · Glass passivated
- High maximum operating temperature
- · Low leakage current
- · Excellent stability
- Guaranteed avalanche energy absorption capability.

### **APPLICATIONS**

- · Car ignition systems
- Automotive applications with extreme temperature requirements.

### **DESCRIPTION**

Rugged glass package, using a high temperature alloyed construction.

This package is hermetically sealed and fatigue free as coefficients of expansion of all used parts are matched. The package is designed to be used in an insulating medium such as resin, oil or SF6 gas.

See also the chapter on custom made high-voltage rectifiers in the "General Part of Handbook SC01".



The cathode is marked by an orange band on the body.

Fig.1 Simplified outline (SOD88A) and symbol.

### **LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.
V <sub>RRM</sub>	repetitive peak reverse voltage		_	3	kV
V <sub>RWM</sub>	crest working reverse voltage		_	3	kV
I <sub>F(AV)</sub>	average forward current		_	100	mA
I <sub>FRM</sub>	repetitive peak forward current		_	5	Α
I <sub>FSM</sub>	non-repetitive peak forward current	$t = 10$ ms half sinewave; $T_j = T_{j \text{ max}}$ prior to surge; $V_R = V_{RWMmax}$	_	15	А
P <sub>RSM</sub>	non-repetitive peak reverse power dissipation	t = 10 μs; triangular pulse; $T_j = T_{j \text{ max}}$ prior to surge	_	3	kW
T <sub>stg</sub>	storage temperature		-65	+200	°C
Tj	junction temperature	continuous	-65	+180	°C
		maximum 30 mins	-65	+200	°C

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Philips Semiconductors Product specification

# High-voltage soft-recovery controlled avalanche rectifier

BYX120G

### **ELECTRICAL CHARACTERISTICS**

 $T_j$  = 25 °C; unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 250 mA	_	_	5	V
V <sub>(BR)R</sub>	reverse avalanche breakdown voltage	I <sub>R</sub> = 0.1 mA	3.5	_	_	kV
I <sub>R</sub>	reverse current	$V_R = V_{RWMmax}$ ; $T_j = 180  ^{\circ}C$	_	_	75	μΑ

### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R <sub>th j-a</sub>	thermal resistance from junction to ambient	$T_{amb} = T_{leads}$	55	K/W

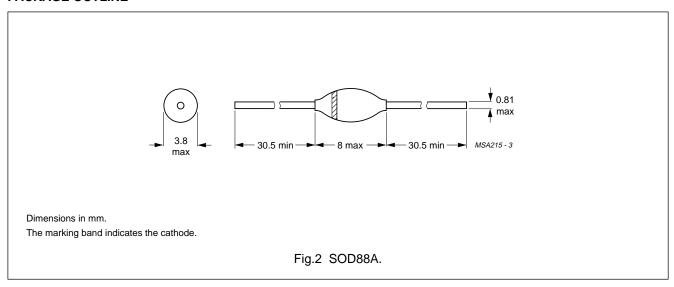
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Philips Semiconductors Product specification

### High-voltage soft-recovery controlled avalanche rectifier

BYX120G

### **PACKAGE OUTLINE**



### **DEFINITIONS**

Data Sheet Status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Limiting values	

Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

### **Application information**

Where application information is given, it is advisory and does not form part of the specification.

### LIFE SUPPORT APPLICATIONS

These products are not designed for use in life support appliances, devices, or systems where malfunction of these products can reasonably be expected to result in personal injury. Philips customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Philips for any damages resulting from such improper use or sale.

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